



Photo Transistor Chip

Features

- Light Activated Photo Transistor Chip
- Planar NPN
- Aluminum Wire bondable
- Backside Metallization - Gold
- Die Attach methods: Eutectic or Epoxy

Electrical Characteristics @ 25°C

SYMBOL	CHARACTERISTIC	CONDITIONS	MIN	TYP	MAX	UNITS
BV_{CEO}	Collector-Emitter Voltage	$I_C = 100 \mu A$	30			Volts
BV_{EBO}	Emitter-Base Voltage	$I_E = 100 \mu A$	4			Volts
BV_{CBO}	Collector-Base Voltage	$I_C = 100 \mu A$	40			Volts
VCE_{SAT}	Collector-Emitter Saturation	$I_C = 1.0 \text{ mA}, I_B = 40 \mu A$			350	mVolts
ID	Collector Current	$V_{CE} = 10 \text{ Volts}$			90	nAmps
h_{FE}	Beta	$V_{CE} = 5 \text{ Volts}, I_B = 4 \mu A$	2,000			